Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

ProASIC3 Flash Family FPGAs
with Optional Soft ARM Support

Features and Benefits

High Capacity
- 15 K to 1 M System Gates
- Up to 144 Kbits of True Dual-Port SRAM
- Up to 300 User I/Os

Reprogrammable Flash Technology
- 130-nm, 7-Layer Metal (6 Copper), Flash-Based CMOS Process
- Instant On Level 0 Support
- Single-Chip Solution
- Retains Programmed Design when Powered Off

High Performance
- 350 MHz System Performance
- 3.3 V, 66 MHz 64-Bit PCI[†]

In-System Programming (ISP) and Security
- ISP Using On-Chip 128-Bit Advanced Encryption Standard (AES) Decryption (except ARM®-enabled ProASIC®3 devices) via JTAG (IEEE 1532–compliant)[†]
- FlashLock® to Secure FPGA Contents

Low Power
- Core Voltage for Low Power
- Support for 1.5 V-Only Systems
- Low-Impedance Flash Switches

High-Performance Routing Hierarchy
- Segmented, Hierarchical Routing and Clock Structure

Advanced I/O
- 700 Mbps DDR, LVDS-Capable I/Os (A3P250 and above)
- 1.5 V, 1.8 V, 2.5 V, and 3.3 V Mixed-Voltage Operation
- Wide Range Power Supply Voltage Support per JESD8-B, Allowing I/Os to Operate from 2.7 V to 3.6 V
- Bank-Selectable I/O Voltages—up to 4 Banks per Chip
- Single-Ended I/O Standards: LVTTL, LVCMOS 3.3 V / 2.5 V / 1.8 V / 1.5 V, 3.3 V PCI / 3.3 V PCI-X[†] and LVCMOS 2.5 V / 5.0 V Input
- Differential I/O Standards: LVPECL, LVDS, B-LVDS, and M-LVDS (A3P250 and above)
- I/O Registers on Input, Output, and Enable Paths
- Hot-Swappable and Cold Sparing I/Os[‡]
- Programmable Output Slew Rate[†] and Drive Strength
- Weak Pull-Up/-Down
- IEEE 1149.1 (JTAG) Boundary Scan Test
- Pin-Compatible Packages across the ProASIC3 Family

Clock Conditioning Circuit (CCC) and PLL[†]
- Six CCC Blocks, One with an Integrated PLL
- Configurable Phase-Shift, Multiply/Divide, Delay Capabilities and External Feedback
- Wide Input Frequency Range (1.5 MHz to 350 MHz)

Embedded Memory[†]
- 1 Kbit of FlashROM User Nonvolatile Memory
- SRAMs and FIFOs with Variable-Aspect-Ratio 4,608-Bit RAM Blocks (×1, ×2, ×4, ×9, and ×18 organizations)[†]
- True Dual-Port SRAM (except ×18)

ARM Processor Support in ProASIC3 FPGAs
- M1 ProASIC3 Devices—ARM®Cortex®-M1 Soft Processor Available with or without Debug

ProASIC3 Devices	A3P015[1]	A3P030	A3P060	A3P125	A3P250	A3P400	A3P600	A3P1000
Cortex-M1 Devices [2]					M1A3P250	M1A3P400	M1A3P600	M1A3P1000
System Gates	15,000	30,000	60,000	125,000	250,000	400,000	600,000	1,000,000
Typical Equivalent Macrocells	128	256	512	1,024	2,048	–	–	–
VersaTiles (D-flip-flops)	384	768	1,536	3,072	6,144	9,216	13,824	24,576
RAM Kbits (1,024 bits)	–	–	18	36	36	54	108	144
4,608-Bit Blocks	–	–	4	8	8	12	24	32
FlashROM Kbits	1	1	1	1	1	1	1	1
Secure (AES) ISP [3]	–	–	Yes	Yes	Yes	Yes	Yes	Yes
Integrated PLL in CCCs	–	–	1	1	1	1	1	1
VersaNet Globals [4]	6	6	18	18	18	18	18	18
I/O Banks	2	2	2	2	4	4	4	4
Maximum User I/Os	49	81	96	133	157	194	235	300

Notes:
1. *A3P015 is not recommended for new designs.*
2. *Refer to the Cortex-M1 product brief for more information.*
3. *AES is not available for Cortex-M1 ProASIC3 devices.*
4. *Six chip (main) and three quadrant global networks are available for A3P060 and above.*
5. *The M1A3P250 device does not support this package.*
6. *For higher densities and support of additional features, refer to the ProASIC3E Flash Family FPGAs datasheet.*
7. *Package not available.*

† *A3P015 and A3P030 devices do not support this feature.*   ‡ *Supported only by A3P015 and A3P030 devices.*

ProASIC3 Devices	A3P015[1]	A3P030	A3P060	A3P125	A3P250	A3P400	A3P600	A3P1000
Cortex-M1 Devices [2]					M1A3P250	M1A3P400	M1A3P600	M1A3P1000
Package Pins								
QFN	QN68	QN48, QN68, QN132[7]	QN132[7]	QN132[7]	QN132[7]			
CS			CS121					
VQFP		VQ100	VQ100	VQ100	VQ100			
TQFP			TQ144	TQ144				
PQFP				PQ208	PQ208	PQ208	PQ208	PQ208
FBGA			FG144	FG144	FG144/256 [5]	FG144/256/484	FG144/256/484	FG144/256/484

Notes:

1. *A3P015 is not recommended for new designs.*
2. *Refer to the Cortex-M1 product brief for more information.*
3. *AES is not available for Cortex-M1 ProASIC3 devices.*
4. *Six chip (main) and three quadrant global networks are available for A3P060 and above.*
5. *The M1A3P250 device does not support this package.*
6. *For higher densities and support of additional features, refer to the ProASIC3E Flash Family FPGAs datasheet.*
7. *Package not available.*

I/Os Per Package [1]

ProASIC3 Devices	A3P015[2]	A3P030	A3P060	A3P125	A3P250 [3]		A3P400 [3]		A3P600		A3P1000	
Cortex-M1 Devices					M1A3P250 [3,5]		M1A3P400 [3]		M1A3P600		M1A3P1000	
	I/O Type											
Package	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O[4]	Differential I/O Pairs	Single-Ended I/O[4]	Differential I/O Pairs	Single-Ended I/O[4]	Differential I/O Pairs	Single-Ended I/O[4]	Differential I/O Pairs
QN48	–	34	–	–	–	–		–	–	–	–	–
QN68	49	49	–	–	–	–	–	–	–	–	–	–
QN132[7]	–	81	80	84	87	19	–	–		–	–	–
CS121	–	–	96	–	–	–	–	–	–	–	–	–
VQ100	–	77	71	71	68	13	–	–		–	–	–
TQ144	–	–	91	100	–	–	–	–	–	–	–	–
PQ208	–	–	–	133	151	34	151	34	154	35	154	35
FG144	–	–	96	97	97	24	97	25	97	25	97	25
FG256[5,6]	–	–	–	–	157	38	178	38	177	43	177	44
FG484[6]	–	–	–	–	–	–	194	38	235	60	300	74

Notes:
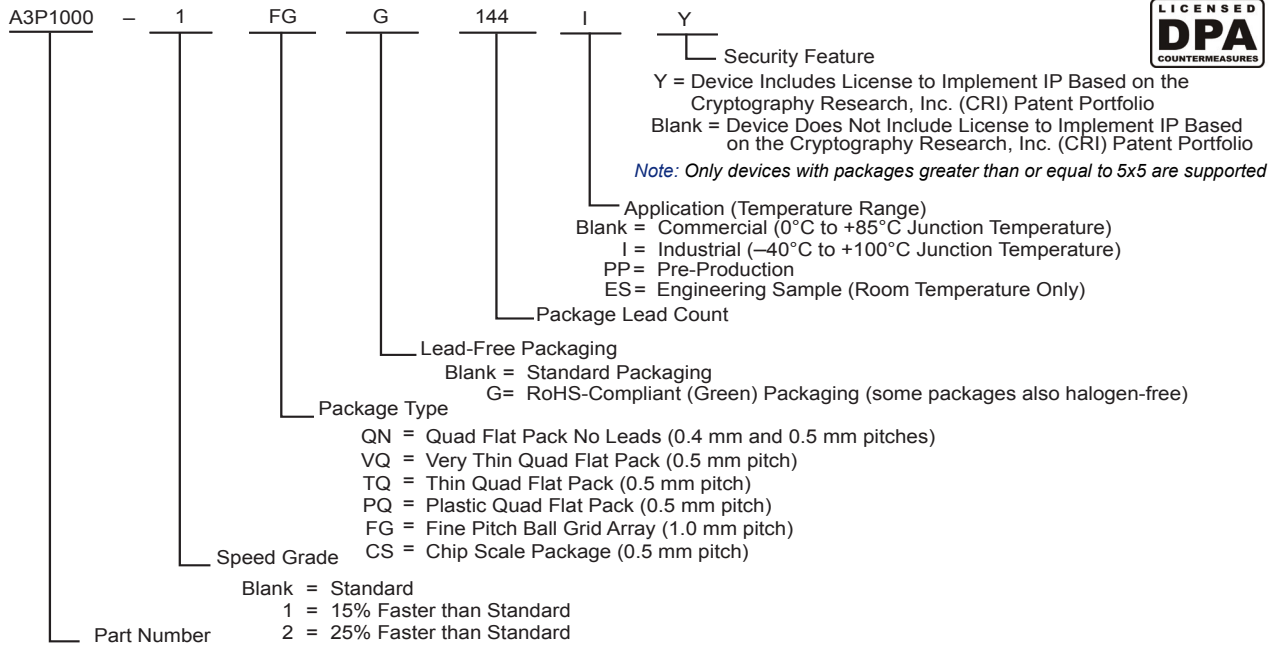1. *When considering migrating your design to a lower- or higher-density device, refer to the ProASIC3 FPGA Fabric User Guide to ensure complying with design and board migration requirements.*
2. *A3P015 is not recommended for new designs.*
3. *For A3P250 and A3P400 devices, the maximum number of LVPECL pairs in east and west banks cannot exceed 15. Refer to the ProASIC3 FPGA Fabric Users Guide for position assignments of the 15 LVPECL pairs.*
4. *Each used differential I/O pair reduces the number of single-ended I/Os available by two.*
5. *The M1A3P250 device does not support FG256 package.*
6. *FG256 and FG484 are footprint-compatible packages.*
7. *Package not available.*

Table 1 • ProASIC3 FPGAs Package Sizes Dimensions

Package	CS121	QN48	QN68	QN132 [*]	VQ100	TQ144	PQ208	FG144	FG256	FG484
Length × Width (mm × mm)	6 × 6	6 × 6	8 × 8	8 × 8	14 × 14	20 × 20	28 × 28	13 × 13	17 × 17	23 × 23
Nominal Area (mm^2)	36	36	64	64	196	400	784	169	289	529
Pitch (mm)	0.5	0.4	0.4	0.5	0.5	0.5	0.5	1.0	1.0	1.0
Height (mm)	0.99	0.90	0.90	0.75	1.00	1.40	3.40	1.45	1.60	2.23

*Note: * Package not available*

ProASIC3 Ordering Information

```
A3P1000    –    1    FG    G    144    I    Y
```

LICENSED DPA COUNTERMEASURES

Security Feature
Y = Device Includes License to Implement IP Based on the
    Cryptography Research, Inc. (CRI) Patent Portfolio
Blank = Device Does Not Include License to Implement IP Based
    on the Cryptography Research, Inc. (CRI) Patent Portfolio
Note: Only devices with packages greater than or equal to 5x5 are supported

Application (Temperature Range)
Blank = Commercial (0°C to +85°C Junction Temperature)
I = Industrial (−40°C to +100°C Junction Temperature)
PP = Pre-Production
ES = Engineering Sample (Room Temperature Only)

Package Lead Count

Lead-Free Packaging
Blank = Standard Packaging
G = RoHS-Compliant (Green) Packaging (some packages also halogen-free)

Package Type
QN = Quad Flat Pack No Leads (0.4 mm and 0.5 mm pitches)
VQ = Very Thin Quad Flat Pack (0.5 mm pitch)
TQ = Thin Quad Flat Pack (0.5 mm pitch)
PQ = Plastic Quad Flat Pack (0.5 mm pitch)
FG = Fine Pitch Ball Grid Array (1.0 mm pitch)
CS = Chip Scale Package (0.5 mm pitch)

Speed Grade
Blank = Standard
1 = 15% Faster than Standard
2 = 25% Faster than Standard

Part Number

ProASIC3 Devices

A3P015 = 15,000 System Gates (A3P015 is not recommended for new designs.)
A3P030 = 30,000 System Gates
A3P060 = 60,000 System Gates
A3P125 = 125,000 System Gates
A3P250 = 250,000 System Gates
A3P400 = 400,000 System Gates
A3P600 = 600,000 System Gates
A3P1000 = 1,000,000 System Gates

ProASIC3 Devices with Cortex-M1

M1A3P250 = 250,000 System Gates
M1A3P400 = 400,000 System Gates
M1A3P600 = 600,000 System Gates
M1A3P1000 = 1,000,000 System Gates

ProASIC3 Device Status

ProASIC3 Devices	Status	Cortex-M1 Devices	Status
A3P015	Not recommended for new designs.		
A3P030	Production		
A3P060	Production		
A3P125	Production		
A3P250	Production	M1A3P250	Production
A3P400	Production	M1A3P400	Production
A3P600	Production	M1A3P600	Production
A3P1000	Production	M1A3P1000	Production

ProASIC3 Device Family Overview

ProASIC3 DC and Switching Characteristics

Pin Descriptions

Package Pin Assignments

Datasheet Information

1 – ProASIC3 Device Family Overview

General Description

ProASIC3, the third-generation family of Microsemi flash FPGAs, offers performance, density, and features beyond those of the ProASIC^PLUS® family. Nonvolatile flash technology gives ProASIC3 devices the advantage of being a secure, low power, single-chip solution that is Instant On. ProASIC3 is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost. These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

ProASIC3 devices offer 1 kbit of on-chip, reprogrammable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on an integrated phase-locked loop (PLL). The A3P015 and A3P030 devices have no PLL or RAM support. ProASIC3 devices have up to 1 million system gates, supported with up to 144 kbits of true dual-port SRAM and up to 300 user I/Os.

ProASIC3 devices support the ARM Cortex-M1 processor. The ARM-enabled devices have Microsemi ordering numbers that begin with M1A3P (Cortex-M1) and do not support AES decryption.

Flash Advantages

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based ProASIC3 devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property (IP) cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The ProASIC3 family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the ProASIC3 family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/ communications, computing, and avionics markets.

Security

The nonvolatile, flash-based ProASIC3 devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. ProASIC3 devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

ProASIC3 devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for intellectual property and configuration data. In addition, all FlashROM data in ProASIC3 devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. The AES standard was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. ProASIC3 devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. ProASIC3 devices with AES-based security provide a high level of protection for remote field updates over public networks such as the Internet, and are designed to ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

ARM-enabled ProASIC3 devices do not support user-controlled AES security mechanisms. Since the ARM core must be protected at all times, AES encryption is always on for the core logic, so bitstreams are always encrypted. There is no user access to encryption for the FlashROM programming data.

Security, built into the FPGA fabric, is an inherent component of the ProASIC3 family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The ProASIC3 family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks.

Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3 device provides the best available security for programmable logic designs.

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based ProASIC3 FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Flash-based ProASIC3 devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based ProASIC3 devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs that are used for these purposes in a system. In addition, glitches and brownouts in system power will not corrupt the ProASIC3 device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based ProASIC3 devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

Firm Errors

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of ProASIC3 flash-based FPGAs. Once it is programmed, the flash cell configuration element of ProASIC3 FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Low Power

Flash-based ProASIC3 devices exhibit power characteristics similar to an ASIC, making them an ideal choice for power-sensitive applications. ProASIC3 devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

ProASIC3 devices also have low dynamic power consumption to further maximize power savings.

Advanced Flash Technology

The ProASIC3 family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

Advanced Architecture

The proprietary ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory[†]
- Extensive CCCs and PLLs[†]
- Advanced I/O structure
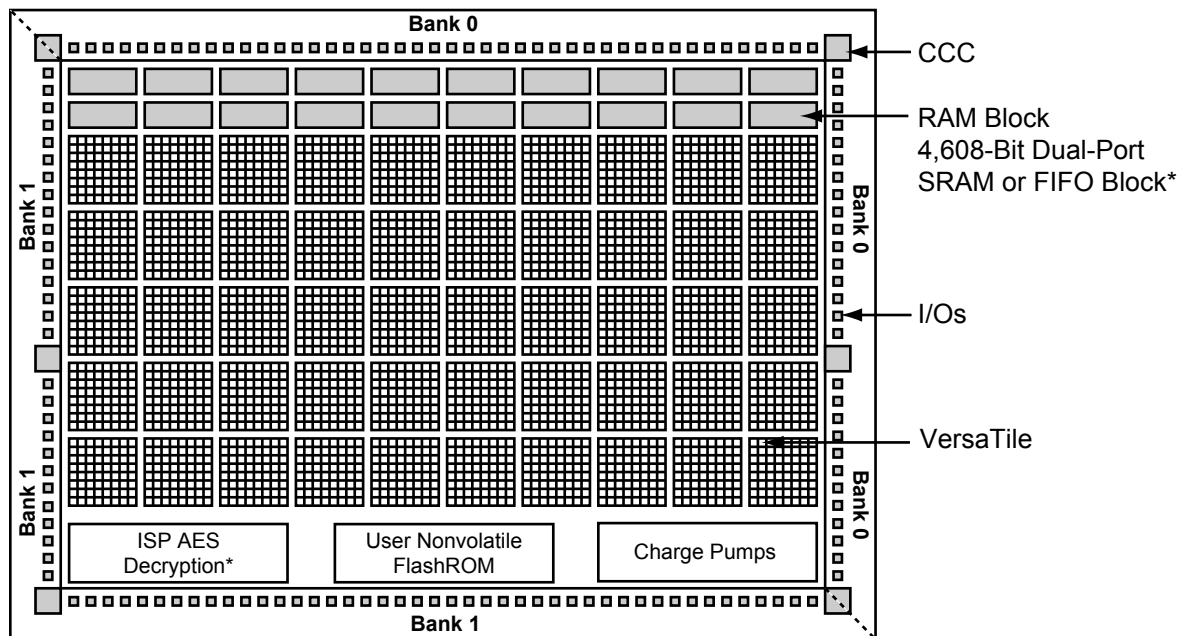
Note: *Not supported by A3P015 and A3P030 devices

Figure 1-1 •   ProASIC3 Device Architecture Overview with Two I/O Banks (A3P015, A3P030, A3P060, and A3P125)

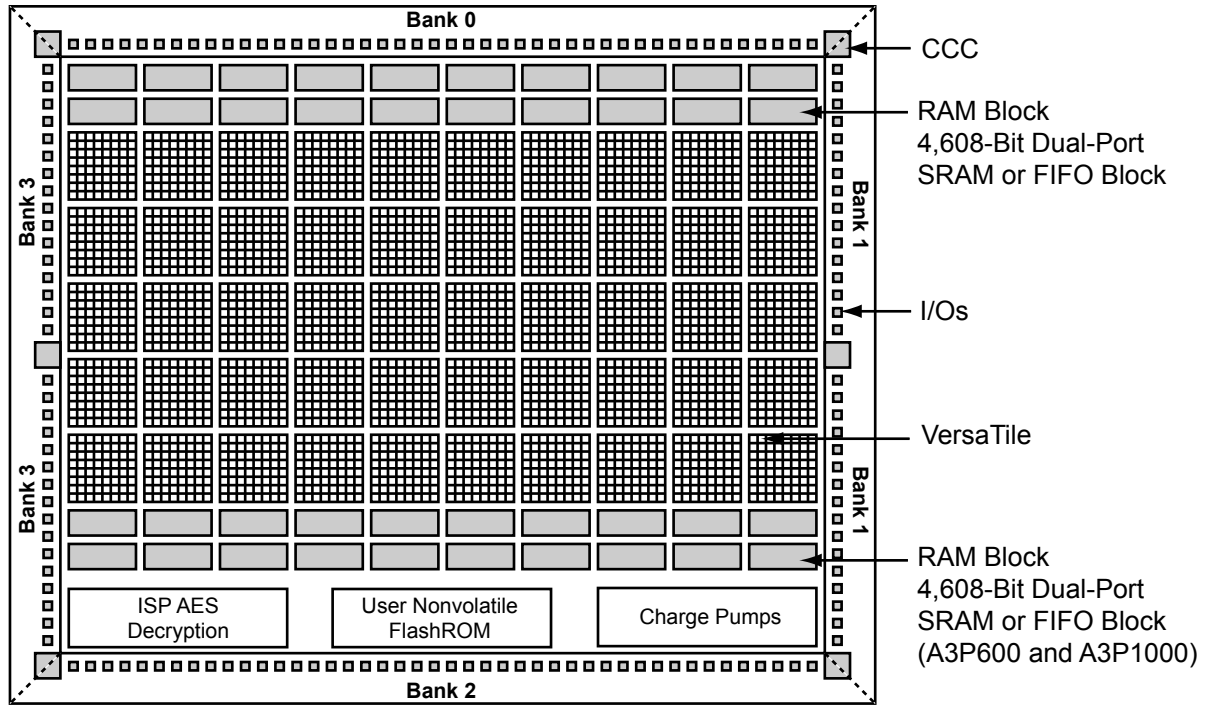† *The A3P015 and A3P030 do not support PLL or SRAM.*

Figure 1-2 • **ProASIC3 Device Architecture Overview with Four I/O Banks (A3P250, A3P600, and A3P1000)**

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the ProASIC3 core tile as either a three-input lookup table (LUT) equivalent or as a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC family of third-generation architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

VersaTiles

The ProASIC3 core consists of VersaTiles, which have been enhanced beyond the ProASIC$^{\underline{PLUS}}$® core tiles. The ProASIC3 VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to Figure 1-3 for VersaTile configurations.

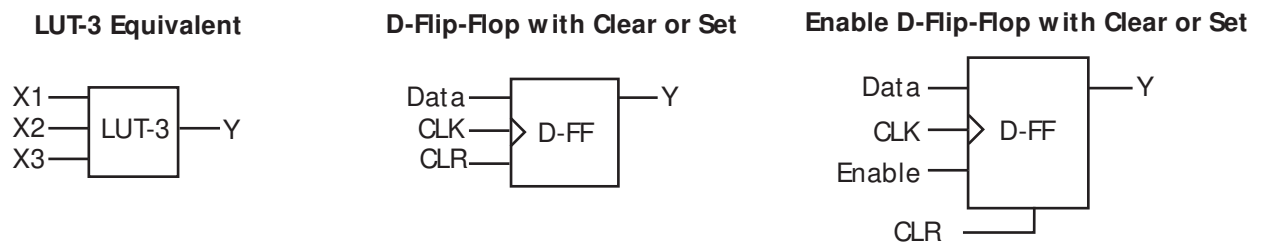*Figure 1-3 •* **VersaTile Configurations**

User Nonvolatile FlashROM

ProASIC3 devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- Internet protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, set-top boxes)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard ProASIC3 IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks (except in the A3P015 and A3P030 devices), as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The ProASIC3 development software solutions, Libero® System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

SRAM and FIFO

ProASIC3 devices (except the A3P015 and A3P030 devices) have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro (except in A3P015 and A3P030 devices).

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

PLL and CCC

ProASIC3 devices provide designers with very flexible clock conditioning capabilities. Each member of the ProASIC3 family contains six CCCs. One CCC (center west side) has a PLL. The A3P015 and A3P030 devices do not have a PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides.

All six CCC blocks are usable; the four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz to 350 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz to 350 MHz
- Clock delay adjustment via programmable and fixed delays from –7.56 ns to +11.12 ns
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time = 300 µs (for PLL only)
- Low power consumption of 5 mW
- Exceptional tolerance to input period jitter— allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × (350 MHz / f_{OUT_CCC}) (for PLL only)

Global Clocking

ProASIC3 devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high fanout nets.

I/Os with Advanced I/O Standards

The ProASIC3 family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). ProASIC3 FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported (Table 1-1).

Table 1-1 • I/O Standards Supported

		I/O Standards Supported		
I/O Bank Type	**Device and Bank Location**	**LVTTL/ LVCMOS**	**PCI/PCI-X**	**LVPECL, LVDS, B-LVDS, M-LVDS**
Advanced	East and west Banks of A3P250 and larger devices	✓	✓	✓
Standard Plus	North and south banks of A3P250 and larger devices All banks of A3P060 and A3P125	✓	✓	Not supported
Standard	All banks of A3P015 and A3P030	✓	Not supported	Not supported

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

ProASIC3 banks for the A3P250 device and above support LVPECL, LVDS, B-LVDS and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Wide Range I/O Support

ProASIC3 devices support JEDEC-defined wide range I/O operation. ProASIC3 supports the JESD8-B specification, covering both 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User's Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-4 on page 1-8).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

    1 – I/O is set to drive out logic High

0 – I/O is set to drive out logic Low

Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming
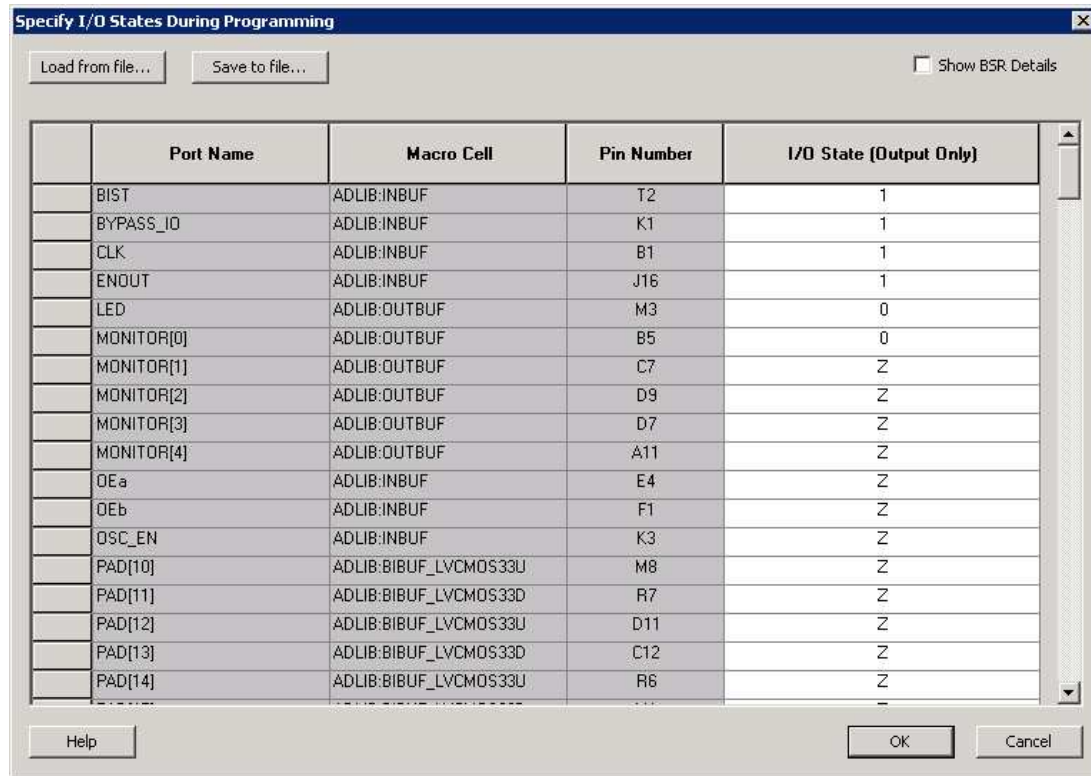
Z -Tristate: I/O is tristated

Figure 1-4 • **I/O States During Programming Window**

6. Click OK to return to the FlashPoint – Programming File Generator window.

Note: I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.

2 – ProASIC3 DC and Switching Characteristics

General Specifications

Operating Conditions

Stresses beyond those listed in Table 2-1 may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in Table 2-2 on page 2-2 is not implied.

Table 2-1 • **Absolute Maximum Ratings**

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O output buffer supply voltage	–0.3 to 3.75	V
VMV	DC I/O input buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)	V
T_{STG} [2]	Storage temperature	–65 to +150	°C
T_J [2]	Junction temperature	+125	°C

Notes:

1. *The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in Table 2-4 on page 2-3.*
2. *VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*
3. *For flash programming and retention maximum limits, refer to Table 2-3 on page 2-3, and for recommended operating limits, refer to Table 2-2 on page 2-2.*

*Table 2-2 •* **Recommended Operating Conditions** [1]

Symbol	Parameters [1]		Commercial	Industrial	Units
T_J	Junction temperature		0 to 85[2]	-40 to 100[2]	°C
VCC[3]	1.5 V DC core supply voltage		1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode	3.15 to 3.45	3.15 to 3.45	V
		Operation [4]	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)		1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV [5]	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	3.3 V wide range DC supply voltage [6]		2.7 to 3.6	2.7 to 3.6	V
	LVDS/B-LVDS/M-LVDS differential I/O		2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. *All parameters representing voltages are measured with respect to GND unless otherwise specified.*

2. *Software Default Junction Temperature Range in the Libero® System-on-Chip (SoC) software is set to 0°C to +70°C for commercial, and -40°C to +85°C for industrial. To ensure targeted reliability standards are met across the full range of junction temperatures, Microsemi recommends using custom settings for temperature range before running timing and power analysis tools. For more information regarding custom settings, refer to the New Project Dialog Box in the Libero SoC Online Help.*

3. *The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-18 on page 2-19.*

4. *VPUMP can be left floating during operation (not programming mode).*

5. *VMV and VCCI should be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*

6. *3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.*

Tj (°C)	HTR Lifetime (yrs)
70	102.7
85	43.8
100	20.0
105	15.6
110	12.3
115	9.7
120	7.7
125	6.2
130	5.0
135	4.0
140	3.3
145	2.7
150	2.2
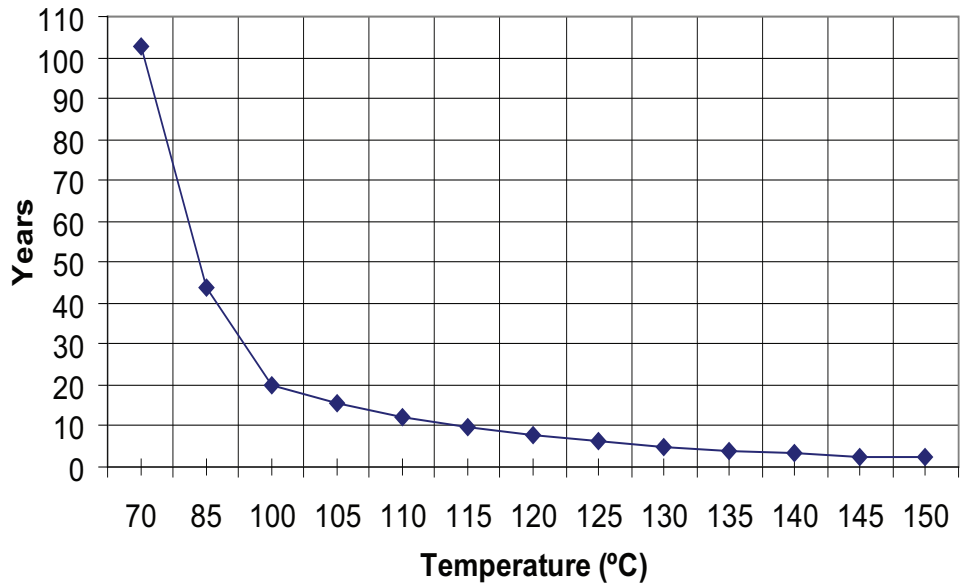
Note: HTR time is the period during which you would not expect a verify failure due to flash cell leakage.

Figure 2-1 • **High-Temperature Data Retention (HTR)**

Table 2-3 • **Flash Programming Limits – Retention, Storage and Operating Temperature[1]**

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T_{STG} (°C)	Maximum Operating Junction Temperature T_J (°C)[2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.*

Table 2-4 • **Overshoot and Undershoot Limits [1]**

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle[2]	Maximum Overshoot/ Undershoot[2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. *Based on reliability requirements at 85°C.*

2. *The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*

3. *This table does not provide PCI overshoot/undershoot limits.*

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges.

In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-2 on page 2-5.

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-2 on page 2-5).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/Down Behavior of Low Power Flash Devices" chapter of the *ProASIC3 FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

Thermal Characteristics

Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Table 2-5 on page 2-6.
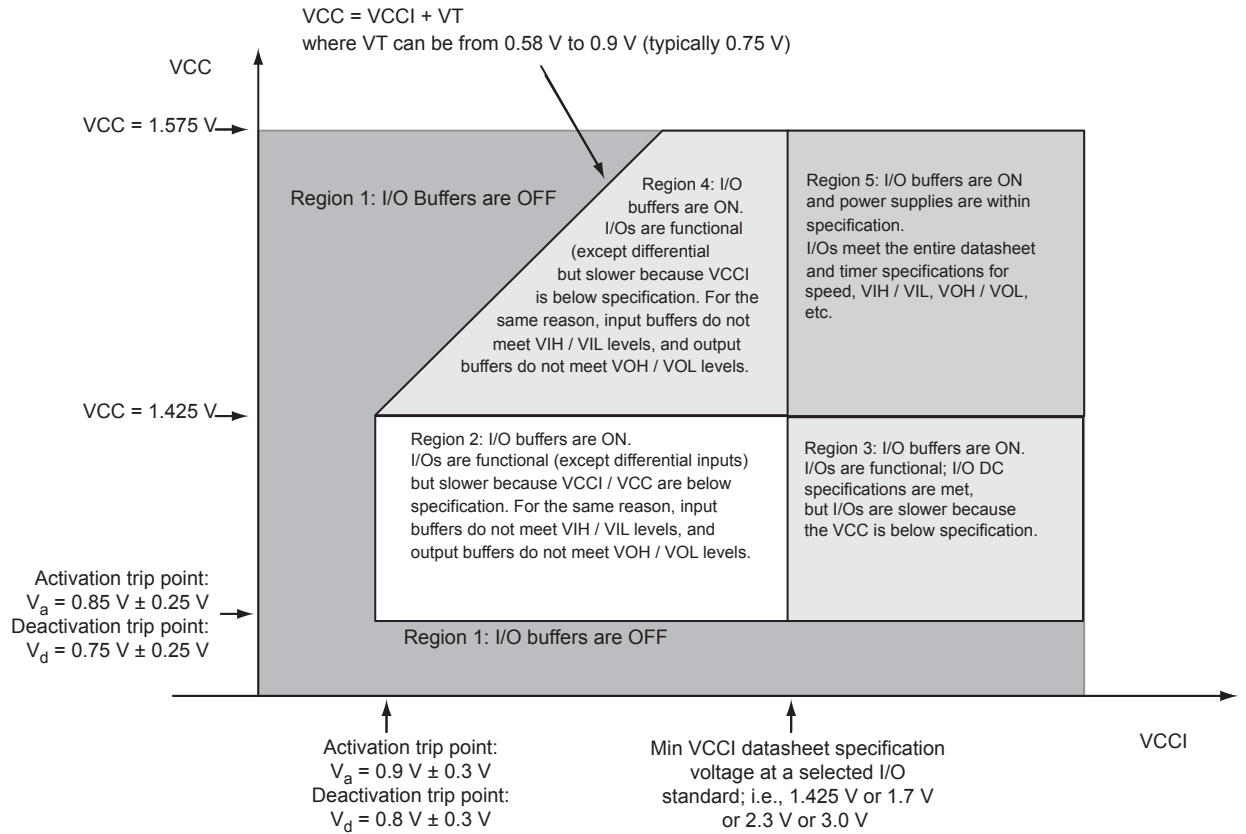
P = Power dissipation

Figure 2-2 • **I/O State as a Function of VCCI and VCC Voltage Levels**

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja}. The thermal characteristics for θ_{ja} are shown for two air flow rates.

The absolute maximum junction temperature is 100°C. EQ 1 shows a sample calculation of the absolute maximum power dissipation allowed for a 484-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja}(\text{°C/W})} = \frac{100°C - 70°C}{20.5°C/W} = 1.463 \ \dot{W}$$

<div align="right">

EQ 1

</div>

Table 2-5 • **Package Thermal Resistivities**

Package Type	Device	Pin Count	θ_{jc}	θ_{ja} Still Air	θ_{ja} 200 ft/min	θ_{ja} 500 ft/min	Units
Quad Flat No Lead	A3P030	132	0.4	21.4	16.8	15.3	°C/W
	A3P060	132	0.3	21.2	16.6	15.0	°C/W
	A3P125	132	0.2	21.1	16.5	14.9	°C/W
	A3P250	132	0.1	21.0	16.4	14.8	°C/W
Very Thin Quad Flat Pack (VQFP)	All devices	100	10.0	35.3	29.4	27.1	°C/W
Thin Quad Flat Pack (TQFP)	All devices	144	11.0	33.5	28.0	25.7	°C/W
Plastic Quad Flat Pack (PQFP)	All devices	208	8.0	26.1	22.5	20.8	°C/W
Fine Pitch Ball Grid Array (FBGA)	See note[*]	144	3.8	26.9	22.9	21.5	°C/W
	See note[*]	256	3.8	26.6	22.8	21.5	°C/W
	See note[*]	484	3.2	20.5	17.0	15.9	°C/W
	A3P1000	144	6.3	31.6	26.2	24.2	°C/W
	A3P1000	256	6.6	28.1	24.4	22.7	°C/W
	A3P1000	484	8.0	23.3	19.0	16.7	°C/W

Note: *This information applies to all ProASIC3 devices except the A3P1000. Detailed device/package thermal information will be available in future revisions of the datasheet.

Temperature and Voltage Derating Factors

Table 2-6 • **Temperature and Voltage Derating Factors for Timing Delays**
(normalized to T_J = 70°C, VCC = 1.425 V)

Array Voltage VCC (V)	Junction Temperature (°C) −40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.88	0.93	0.95	1.00	1.02	1.04
1.500	0.83	0.88	0.90	0.95	0.96	0.98
1.575	0.80	0.84	0.87	0.91	0.93	0.94

Calculating Power Dissipation

Quiescent Supply Current

Table 2-7 • **Quiescent Supply Current Characteristics**

	A3P015	A3P030	A3P060	A3P125	A3P250	A3P400	A3P600	A3P1000
Typical (25°C)	2 mA	2 mA	2 mA	2 mA	3 mA	3 mA	5 mA	8 mA
Max. (Commercial)	10 mA	10 mA	10 mA	10 mA	20 mA	20 mA	30 mA	50 mA
Max. (Industrial)	15 mA	15 mA	15 mA	15 mA	30 mA	30 mA	45 mA	75 mA

Note: IDD Includes VCC, VPUMP, VCCI, and VMV currents. Values do not include I/O static contribution, which is shown in Table 2-11 and Table 2-12 on page 2-9.

Power per I/O Pin

Table 2-8 • **Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Advanced I/O Banks**

	VMV (V)	Static Power P_{DC2} (mW) [1]	Dynamic Power PAC9 (μW/MHz) [2]
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	–	16.22
3.3 V LVCMOS Wide Range[3]	3.3	–	16.22
2.5 V LVCMOS	2.5	–	5.12
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.45
3.3 V PCI	3.3	–	18.11
3.3 V PCI-X	3.3	–	18.11
Differential			
LVDS	2.5	2.26	1.20
LVPECL	3.3	5.72	1.87

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-9 • **Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard Plus I/O Banks**

	VMV (V)	Static Power PDC2 (mW) [1]	Dynamic Power PAC9 (μW/MHz) [2]
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	–	16.23
3.3 V LVCMOS Wide Range[3]	3.3	–	16.23

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-9 • **Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard Plus I/O Banks**

	VMV (V)	Static Power PDC2 (mW) [1]	Dynamic Power PAC9 (µW/MHz) [2]
2.5 V LVCMOS	2.5	–	5.14
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.48
3.3 V PCI	3.3	–	18.13
3.3 V PCI-X	3.3	–	18.13

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-10 • **Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard I/O Banks**

	VMV (V)	Static Power PDC2 (mW) [1]	Dynamic Power PAC9 (µW/MHz) [2]
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	–	17.24
3.3 V LVCMOS Wide Range[3]	3.3	–	17.24
2.5 V LVCMOS	2.5	–	5.19
1.8 V LVCMOS	1.8	–	2.18
1.5 V LVCMOS (JESD8-11)	1.5	–	1.52

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-11 • **Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1]**
Applicable to Advanced I/O Banks

	C$_{LOAD}$ (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	–	468.67
3.3 V LVCMOS Wide Range[4]	35	3.3	–	468.67
2.5 V LVCMOS	35	2.5	–	267.48
1.8 V LVCMOS	35	1.8	–	149.46
1.5 V LVCMOS (JESD8-11)	35	1.5	–	103.12
3.3 V PCI	10	3.3	–	201.02
3.3 V PCI-X	10	3.3	–	201.02
Differential				
LVDS	–	2.5	7.74	88.92
LVPECL	–	3.3	19.54	166.52

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC3 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCC and VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-12 • **Summary of I/O Output Buffer Power (Per Pin) – Default I/O Software Settings[1]**
Applicable to Standard Plus I/O Banks

	C$_{LOAD}$ (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	–	452.67
3.3 V LVCMOS Wide Range[4]	35	3.3	–	452.67
2.5 V LVCMOS	35	2.5	–	258.32
1.8 V LVCMOS	35	1.8	–	133.59
1.5 V LVCMOS (JESD8-11)	35	1.5	–	92.84
3.3 V PCI	10	3.3	–	184.92
3.3 V PCI-X	10	3.3	–	184.92

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *P_{DC3} is the static power (where applicable) measured on VMV.*
3. *P_{AC10} is the total dynamic power measured on VCC and VMV.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-13 • **Summary of I/O Output Buffer Power (Per Pin) – Default I/O Software Settings** [1]
Applicable to Standard I/O Banks

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW) [2]	Dynamic Power PAC10 (µW/MHz) [3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	–	431.08
3.3 V LVCMOS Wide Range[4]	35	3.3	–	431.08
2.5 V LVCMOS	35	2.5	–	247.36
1.8 V LVCMOS	35	1.8	–	128.46
1.5 V LVCMOS (JESD8-11)	35	1.5	–	89.46

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.

2. P_{DC3} is the static power (where applicable) measured on VCCI.

3. P_{AC10} is the total dynamic power measured on VCC and VCCI.

4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

Power Consumption of Various Internal Resources

Table 2-14 • **Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices**

Parameter	Definition	Device Specific Dynamic Contributions (µW/MHz)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PAC1	Clock contribution of a Global Rib	14.50	12.80	12.80	11.00	11.00	9.30	9.30	9.30
PAC2	Clock contribution of a Global Spine	2.48	1.85	1.35	1.58	0.81	0.81	0.41	0.41
PAC3	Clock contribution of a VersaTile row	0.81							
PAC4	Clock contribution of a VersaTile used as a sequential module	0.12							
PAC5	First contribution of a VersaTile used as a sequential module	0.07							
PAC6	Second contribution of a VersaTile used as a sequential module	0.29							
PAC7	Contribution of a VersaTile used as a combinatorial Module	0.29							
PAC8	Average contribution of a routing net	0.70							
PAC9	Contribution of an I/O input pin (standard dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PAC10	Contribution of an I/O output pin (standard dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic contribution for PLL	2.60							

Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.*

Table 2-15 • **Different Components Contributing to the Static Power Consumption in ProASIC3 Devices**

Parameter	Definition	Device Specific Static Power (mW)							
		A3P1000	A3P600	A3P400	A3P250	A3P125	A3P060	A3P030	A3P015
PDC1	Array static power in Active mode	See Table 2-7 on page 2-7.							
PDC2	I/O input pin static power (standard-dependent)	See Table 2-8 on page 2-7 through Table 2-10 on page 2-8.							
PDC3	I/O output pin static power (standard-dependent)	See Table 2-11 on page 2-9 through Table 2-13 on page 2-10.							
PDC4	Static PLL contribution	2.55 mW							
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-7 on page 2-7.							

Note: **For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi Power spreadsheet calculator or SmartPower tool in Libero SoC software.*

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-16 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-17 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-17 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = P_{DC1} + N_{INPUTS} * P_{DC2} + N_{OUTPUTS} * P_{DC3}$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (P_{AC1} + N_{SPINE}*P_{AC2} + N_{ROW}*P_{AC3} + N_{S-CELL} * P_{AC4}) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide.*

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3 FPGA Fabric User's Guide*.